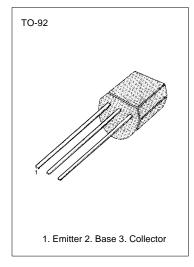
NPN EPITAXIAL SILICON TRANSISTOR

AMPLIFIER TRANSITOR

ABSOLUTE MAXIMUM RATINGS (T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage Collector-Emitter Voltage Emitter-Base Voltage Collector Dissipation ($T_A=25^{\circ}C$) Derate above $25^{\circ}C$ Collector Dissipation ($T_A=25^{\circ}C$) Derate above $25^{\circ}C$ Junction Temperature Storage Temperature Thermal Resistance, Junction to Case Thermal Resistance, Junction to Ambient	VCBO VCEO PC PC TJ TSTG Rth(j-c) Rth(j-a)	30 25 3.0 350 2.8 1.0 8.0 150 -55~150 125 357	°°°°°°°°°°°°°°°°°°°°°°°°°°°°°°°°°°°°°



ELECTRICAL CHARACTERISTICS (T_A=25°C)

Characteristic	Symbol	Test Conditions	Min	Max	Unit
Collector-Baser Breakdown Voltage Collector-Emitter Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current Emitter Cut-off Current DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter On Voltage Current Gain Bandwidth Product Collector Base Capacitance Collector Base Feedback Capacitance	$\begin{array}{c} BV_{CBO}\\ BV_{CEO}\\ BV_{EBO}\\ I_{CBO}\\ I_{EBO}\\ h_{FE}\\ V_{CE}\left(sat\right)\\ V_{BE}\left(sat\right)\\ C_{CB}\\ C_{RB} \end{array}$	$ \begin{array}{l} I_{C} = 100 \mu A, \ I_{E} = 0 \\ I_{C} = 1 m A, \ I_{B} = 0 \\ I_{E} = 10 \mu A, \ I_{C} = 0 \\ V_{CB} = 25 V, \ I_{C} = 0 \\ V_{CE} = 2V, \ I_{C} = 0 \\ V_{CE} = 10V, \ I_{C} = 4 m A \\ I_{C} = 4 m A, \ I_{B} = 0.4 m A \\ V_{CE} = 10V, \ I_{C} = 4 m A \\ V_{CE} = 10V, \ I_{C} = 4 m A \\ V_{CB} = 10V, \ I_{C} = 10 M Hz \\ \end{array} $	30 25 3.0 60 650	100 100 0.5 0.95 0.7	V V nA nA V V MHz pF
: KSP10 : KSP11 Collector Base Time Constant	Cc·rbb′	V _{CB} =10V, I _C =4mA, f=31.8MHz	0.35 0.6	0.65 0.9 9.0	pF pF ps

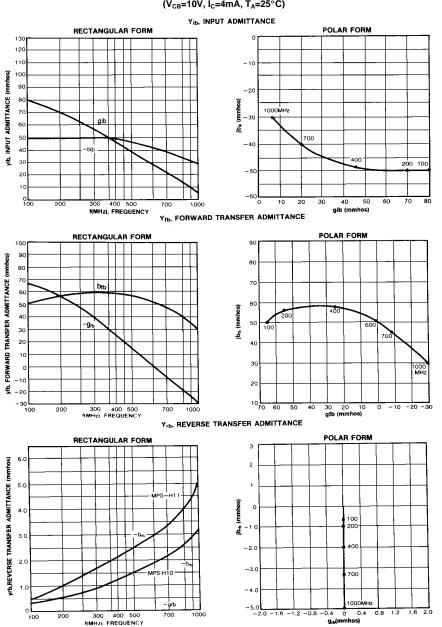
* Pulse Test: PW≤300µs, Duty Cycle≤2%



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 $\begin{array}{l} \mbox{COMMON-BASE y PARAMETERS Vs FREQUENCY} \\ (V_{CB}\mbox{=}10V, \mbox{ I}_{C}\mbox{=}4mA, \mbox{ T}_{A}\mbox{=}25^{\circ}\mbox{C}) \end{array}$



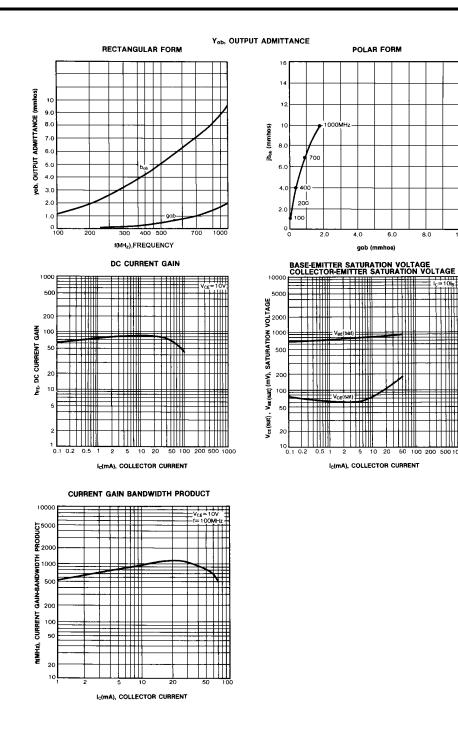
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8.0

100 200 500 10

10





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